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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/681,922	10/09/2003	Hwa-Young Kang	5000-1-332 DIV	7727
33942 7	7590 02/05/2004		EXAMINER ·	
CHA & REITER, LLC 210 ROUTE 4 EAST STE 103			MULPURI, SAVITRI	
PARAMUS, NJ 07652			ART UNIT	PAPER NUMBER
<b>-</b>			2812	

DATE MAILED: 02/05/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)		
	10/681,922	KANG ET AL.		
Office Action Summary	Examiner	Art Unit		
	Savitri Mulpuri	2812		
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address		
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period w - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be ting within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from a cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).		
Status				
1) Responsive to communication(s) filed on 09 O	ctober 2003.			
2a) This action is <b>FINAL</b> . 2b) ⊠ This	action is non-final.			
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213.				
Disposition of Claims	•			
4) ☐ Claim(s) 7-14 is/are pending in the application. 4a) Of the above claim(s) is/are withdray 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 7-14 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and/o	wn from consideration.			
Application Papers				
9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) acc Applicant may not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Example 11.	epted or b) objected to by the drawing(s) be held in abeyance. Se tion is required if the drawing(s) is ob	e 37 CFR 1.85(a). jected to. See 37 CFR 1.121(d).		
Priority under 35 U.S.C. § 119				
a) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of:  1. Certified copies of the priority document 2. Certified copies of the priority document 3. Copies of the certified copies of the priority application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Applicat rity documents have been receive u (PCT Rule 17.2(a)).	ion No. <u>10/346,315</u> . ed in this National Stage		
Attachment(s)  1) Notice of References Cited (PTO-892)  2) Notice of Draftsperson's Patent Drawing Review (PTO-948)  3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)  Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail D 5) Notice of Informal F 6) Other:			

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## **DETAILED ACTION**

## Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 7-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Admitted prior art in combination with Park et al (US 5,877,040) and Tanaka (JP361280686A)

Admitted prior art teaches a method and product of photodiode by successively forming buffer layer "2"; light absorbing layer "3"; epitaxial layer "4" by metal organic chemical vapor deposition on a substrate "1"; forming patterned silicon nitride layer on epitaxial layer to expose part of the epitaxial layer; performing diffusion process using patterned silicon nitride as mask to form diffusion region on the active region "9"; forming top metal electrode on surface of the nitride and on the surface of the active region and bottom metal electrode on the bottom surface of the substrate. Admitted prior art inherently teach InP epitaxial layer and Zn diffusion. Admitted prior art does not teach selectively etching the epitaxial layer of the active region to form convex-lens shape region.

Park et al teaches forming active region of the photodiode in a convexlens shape "34" by etching; forming doped region "36" on the top of the convex shape region. Park et al specifically teach the convex shape portion is part of the photodiode and not external to the photodiode. Park teaches patterned photosentive mask "52" for forming convex shape photodiode, wherein mask "52" is lens and it photosenstive. Park teaches forming convex shape diode region contributes to enhanced photosensitivity (see 3A-3J and related description, col. 1, lines 60-65). It would have been obvious to one of ordinary skill in the art to use convex shaped photodiode for enhanced photosensitivity.

Park does not teach forming covex shape by selectively etching the active region "34" by using methanol bromide as an etchant.

Tanaka teaches forming convex shape from InP based layer by using methanol bromide as an etchant. It would have been obvious to one of ordinary skill in the art to use methanol bromide in the invention of Admitted prior art to etch the epitaxial layer active region to form convex shape photodiode by using methanol bromide as suggested by Tanaka.

## Conclusion

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Prior art generally teach forming photodiode.

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Savitri Mulpuri whose telephone number is 703-272-1677. The examiner can normally be reached on Mon-Fri from 8 to 4.30 a.m.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Niebling, can be reached on 703-272-1679. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Savitri Mulpuri
Primary Examiner
Art Unit 2812